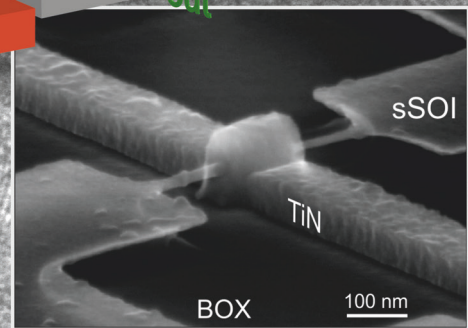
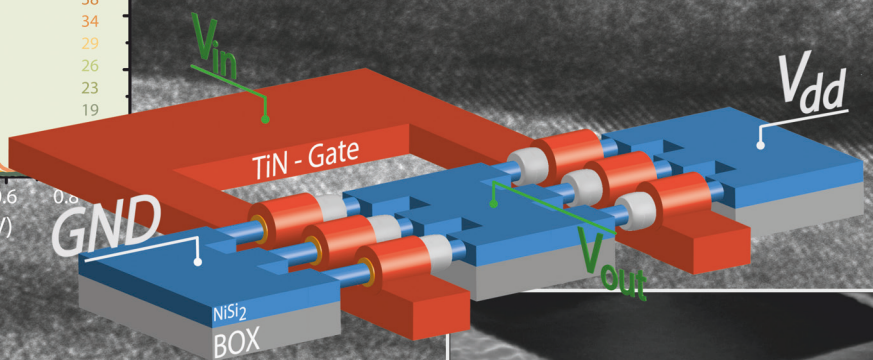
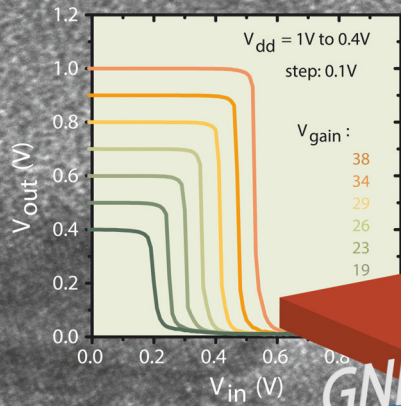


# Gate-All-Around Silicon Nanowire Tunnel FETs for Low Power Applications

Gia Vinh Luong



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